

# FX6KMJ-2

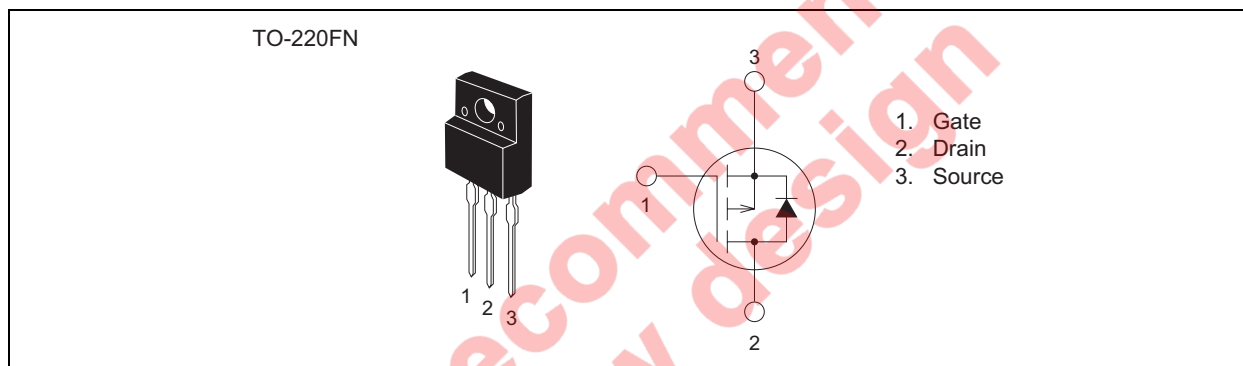
High-Speed Switching Use  
Pch Power MOS FET

REJ03G0262-0100  
Rev.1.00  
Aug.20.2004

## Features

- Drive voltage : 4 V
- $V_{DSS}$  : - 100 V
- $r_{DS(ON)(max)}$  : 0.58  $\Omega$
- $I_D$  : - 6 A
- Recovery Time of the Integrated Fast Recovery Diode (TYP.) : 80 ns

## Outline



## Applications

Motor control, lamp control, solenoid control, DC-DC converters, etc.

## Maximum Ratings

( $T_c = 25^\circ\text{C}$ )

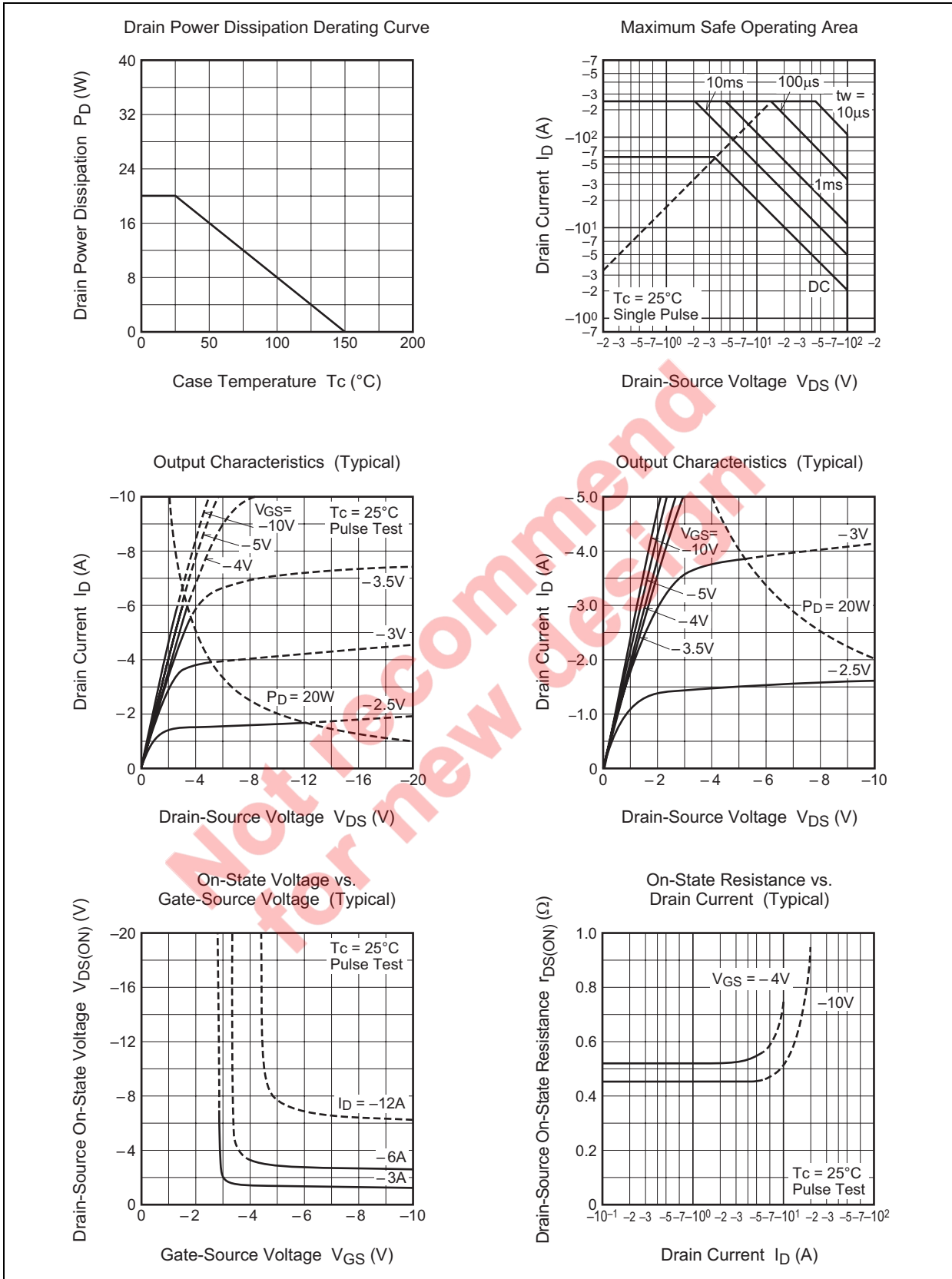
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	$V_{DSS}$	-100	V	$V_{GS} = 0\text{ V}$
Gate-source voltage	$V_{GSS}$	$\pm 20$	V	$V_{DS} = 0\text{ V}$
Drain current	$I_D$	-6	A	
Drain current (Pulsed)	$I_{DM}$	-24	A	
Avalanche current (Pulsed)	$I_{DA}$	-6	A	$L = 100\ \mu\text{H}$
Source current	$I_S$	-6	A	
Source current (Pulsed)	$I_{SM}$	-24	A	
Maximum power dissipation	$P_D$	20	W	
Channel temperature	$T_{ch}$	- 55 to +150	$^\circ\text{C}$	
Storage temperature	$T_{stg}$	- 55 to +150	$^\circ\text{C}$	
Isolation voltage	Viso	2000	V	AC 1 minute, Terminal to case
Mass	—	2.0	g	Typical value

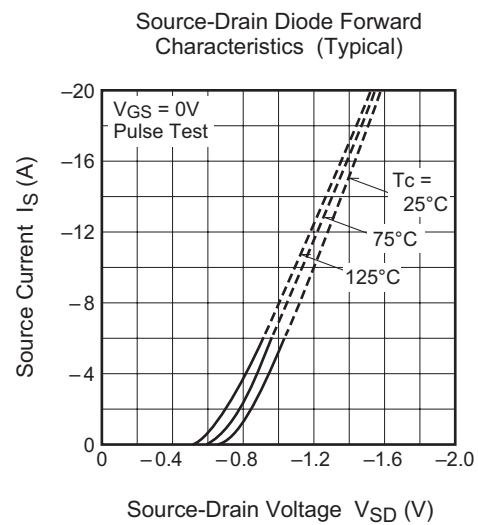
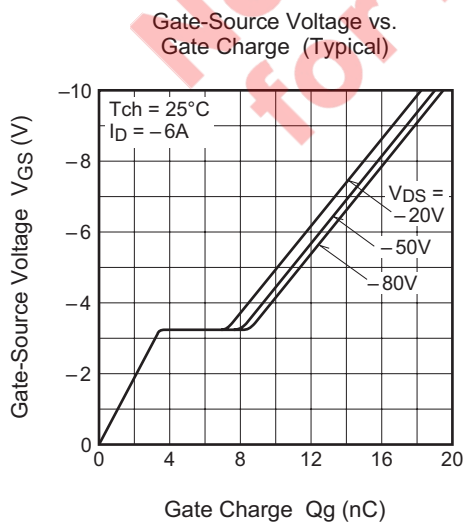
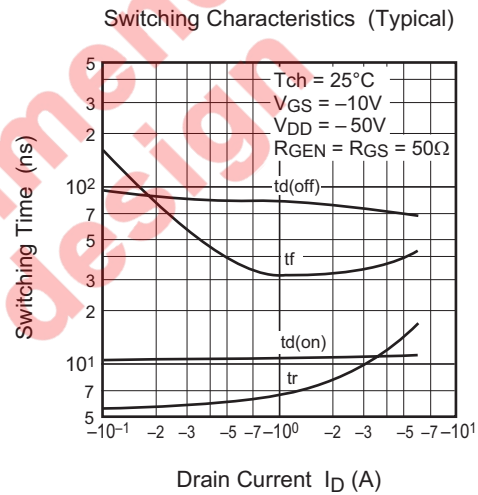
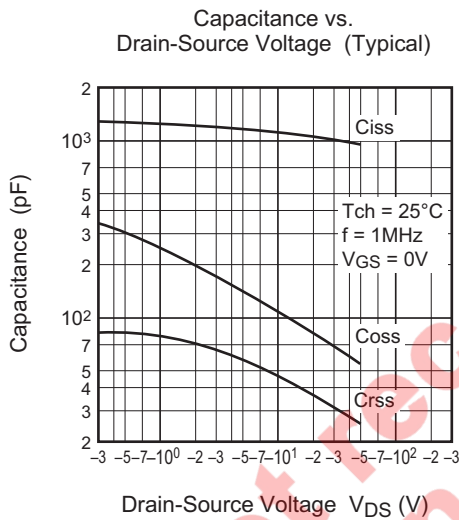
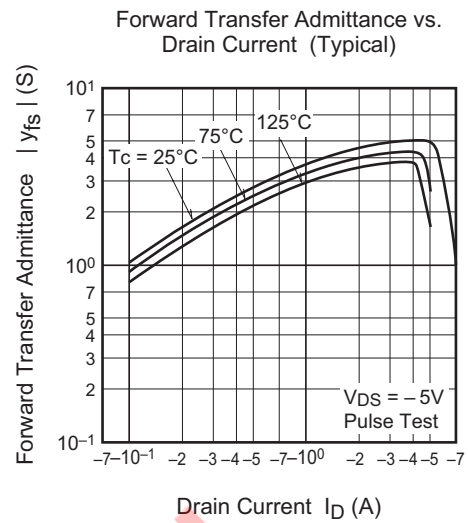
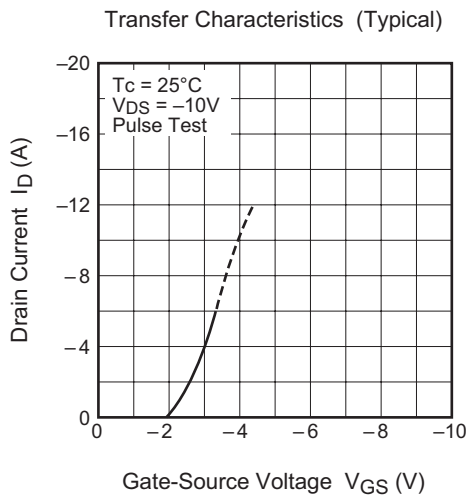
## Electrical Characteristics

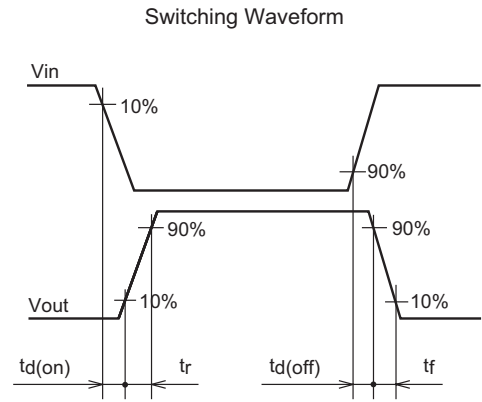
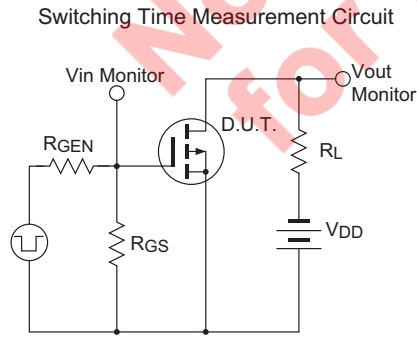
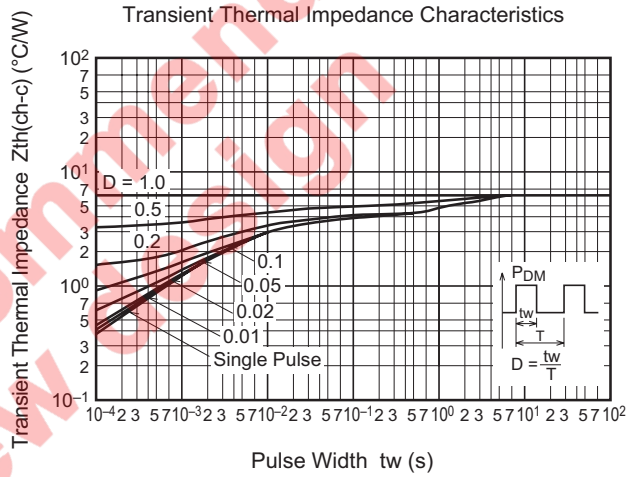
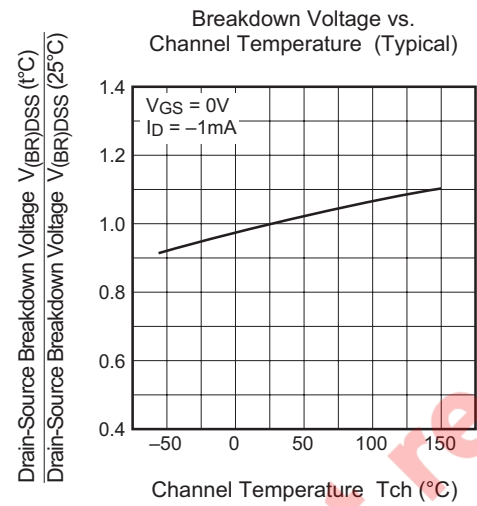
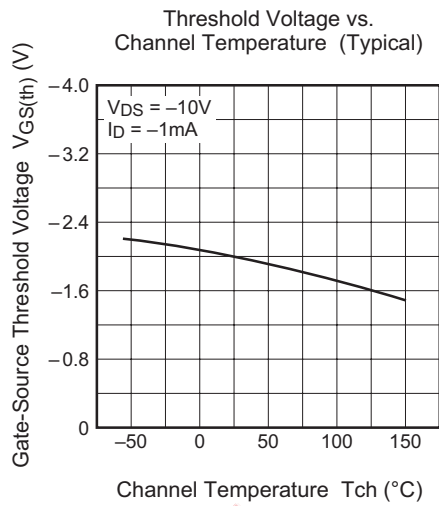
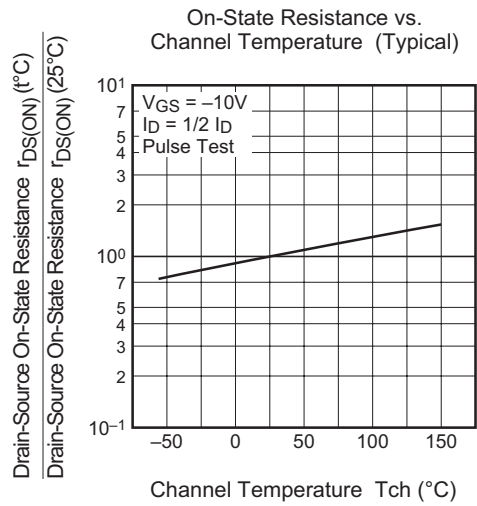
(T<sub>ch</sub> = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test conditions
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	-100	—	—	V	I <sub>D</sub> = -1 mA, V <sub>GS</sub> = 0 V
Gate-source leakage current	I <sub>GSS</sub>	—	—	±0.1	μA	V <sub>GS</sub> = ±20 V, V <sub>DS</sub> = 0 V
Drain-source leakage current	I <sub>DSS</sub>	—	—	-0.1	mA	V <sub>DS</sub> = -100 V, V <sub>GS</sub> = 0 V
Gate-source threshold voltage	V <sub>GS(th)</sub>	-1.0	-1.5	-2.0	V	I <sub>D</sub> = -1 mA, V <sub>DS</sub> = -10 V
Drain-source on-state resistance	r <sub>DS(ON)</sub>	—	0.46	0.58	Ω	I <sub>D</sub> = -3 A, V <sub>GS</sub> = -10 V
Drain-source on-state resistance	r <sub>DS(ON)</sub>	—	0.55	0.72	Ω	I <sub>D</sub> = -3 A, V <sub>GS</sub> = -4 V
Drain-source on-state voltage	V <sub>DS(ON)</sub>	—	-1.38	-1.74	V	I <sub>D</sub> = -3 A, V <sub>GS</sub> = -10 V
Forward transfer admittance	y <sub>fs</sub>	—	4.7	—	S	I <sub>D</sub> = -3 A, V <sub>DS</sub> = -5 V
Input capacitance	C <sub>iss</sub>	—	1110	—	pF	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1MHz
Output capacitance	C <sub>oss</sub>	—	108	—	pF	
Reverse transfer capacitance	C <sub>rss</sub>	—	44	—	pF	
Turn-on delay time	t <sub>d(on)</sub>	—	9	—	ns	V <sub>DD</sub> = -50 V, I <sub>D</sub> = -3 A, V <sub>GS</sub> = -10 V, R <sub>GEN</sub> = R <sub>GS</sub> = 50 Ω
Rise time	t <sub>r</sub>	—	8	—	ns	
Turn-off delay time	t <sub>d(off)</sub>	—	72	—	ns	
Fall time	t <sub>f</sub>	—	33	—	ns	
Source-drain voltage	V <sub>SD</sub>	—	-1.0	-1.5	V	I <sub>S</sub> = -3 A, V <sub>GS</sub> = 0 V
Thermal resistance	R <sub>th(ch-c)</sub>	—	—	6.25	°C/W	Channel to case
Reverse recovery time	t <sub>rr</sub>	—	80	—	ns	I <sub>S</sub> = -6 A, dis/dt = 100 A/μs

Performance Curves







## Package Dimensions

**TO-220FN**

EIAJ Package Code	JEDEC Code	Mass (g) (reference value)	Lead Material
—	—	2.0	Cu alloy

Note 1) The dimensional figures indicate representative values unless otherwise the tolerance is specified.

Symbol	Dimension in Millimeters		
	Min	Typ	Max
A	—	—	—
A1	—	—	—
A2	—	—	—
b	—	—	—
D	—	—	—
E	—	—	—
e	—	—	—
x	—	—	—
y	—	—	—
y1	—	—	—
ZD	—	—	—
ZE	—	—	—

## Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	50	Type name	FX6KMJ-2
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	FX6KMJ-2-A8

Note : Please confirm the specification about the shipping in detail.

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